Andrew Dzurak

List of Publications by Year
in descending order

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187	12,459	34016	24915
papers	citations	52 h-index	109 g-index

189	189	189	6144
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	The Australian National Fabrication Facility: Micro/nanotechnologies from Concept to Translation to End Users. Advanced Functional Materials, 2022, 32, .	7.8	0
2	Precision tomography of a three-qubit donor quantum processor in silicon. Nature, 2022, 601, 348-353.	13.7	118
3	Development of an Undergraduate Quantum Engineering Degree. IEEE Transactions on Quantum Engineering, 2022, 3, 1-10.	2.9	8
4	Materials for Silicon Quantum Dots and their Impact on Electron Spin Qubits. Advanced Functional Materials, 2022, 32, .	7.8	18
5	Exchange Coupling in a Linear Chain of Three Quantum-Dot Spin Qubits in Silicon. Nano Letters, 2021, 21, 1517-1522.	4.5	24
6	Pauli Blockade in Silicon Quantum Dots with Spin-Orbit Control. PRX Quantum, 2021, 2, .	3.5	36
7	Roadmap on quantum nanotechnologies. Nanotechnology, 2021, 32, 162003.	1.3	45
8	Bell-state tomography in a silicon many-electron artificial molecule. Nature Communications, 2021, 12, 3228.	5.8	17
9	A High-Sensitivity Charge Sensor for Silicon Qubits above 1 K. Nano Letters, 2021, 21, 6328-6335.	4.5	6
10	Coherent spin qubit transport in silicon. Nature Communications, 2021, 12, 4114.	5.8	53
11	Single-electron spin resonance in a nanoelectronic device using a global field. Science Advances, 2021, 7, .	4.7	31
12	Conditional quantum operation of two exchange-coupled single-donor spin qubits in a MOS-compatible silicon device. Nature Communications, 2021, 12, 181.	5.8	34
13	Electrical control of the <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math> tensor of the first hole in a silicon MOS quantum dot. Physical Review B, 2021, 104, .	1.1	23
14	Scaling silicon-based quantum computing using CMOS technology. Nature Electronics, 2021, 4, 872-884.	13.1	84
15	Pulse engineering of a global field for robust and universal quantum computation. Physical Review A, 2021, 104, .	1.0	20
16	Quantum computation protocol for dressed spins in a global field. Physical Review B, 2021, 104, .	1.1	15
17	Silicon-based Quantum Computing: High-density, High-temperature Qubits. , 2021, , .		1
18	A silicon quantum-dot-coupled nuclear spin qubit. Nature Nanotechnology, 2020, 15, 13-17.	15.6	60

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19	Single-Electron Operation of a Silicon-CMOS 2 Ã— 2 Quantum Dot Array with Integrated Charge Sensing. Nano Letters, 2020, 20, 7882-7888.	4.5	21
20	Coherent electrical control of a single high-spin nucleus in silicon. Nature, 2020, 579, 205-209.	13.7	79
21	Controllable freezing of the nuclear spin bath in a single-atom spin qubit. Science Advances, 2020, 6, .	4.7	19
22	Coherent spin control of s-, p-, d- and f-electrons in a silicon quantum dot. Nature Communications, 2020, 11, 797.	5.8	51
23	Operation of a silicon quantum processor unit cell above one kelvin. Nature, 2020, 580, 350-354.	13.7	214
24	Silicon integration for quantum sensing. Nature Electronics, 2019, 2, 266-267.	13.1	4
25	Electron spin relaxation of single phosphorus donors in metal-oxide-semiconductor nanoscale devices. Physical Review B, 2019, 99, .	1.1	22
26	Geometric formalism for constructing arbitrary single-qubit dynamically corrected gates. Physical Review A, 2019, 99, .	1.0	31
27	Controlling Spin-Orbit Interactions in Silicon Quantum Dots Using Magnetic Field Direction. Physical Review X, 2019, 9, .	2.8	42
28	Fidelity benchmarks for two-qubit gates in silicon. Nature, 2019, 569, 532-536.	13.7	271
29	Silicon qubit fidelities approaching incoherent noise limits via pulse engineering. Nature Electronics, 2019, 2, 151-158.	13.1	135
30	Gate-based single-shot readout of spins in silicon. Nature Nanotechnology, 2019, 14, 437-441.	15.6	109
31	High-fidelity and robust two-qubit gates for quantum-dot spin qubits in silicon. Physical Review A, 2019, 99, .	1.0	15
32	Single-spin qubits in isotopically enriched silicon at low magnetic field. Nature Communications, 2019, 10, 5500.	5.8	48
33	Waiting time distributions in a two-level fluctuator coupled to a superconducting charge detector. Physical Review Research, 2019, 1, .	1.3	11
34	Electron <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math> -factor of valley states in realistic silicon quantum dots. Physical Review B, 2018, 98, .	1.1	36
35	Coherent control via weak measurements in P31 single-atom electron and nuclear spin qubits. Physical Review B, 2018, 98, .	1.1	15
36	Assessment of a Silicon Quantum Dot Spin Qubit Environment via Noise Spectroscopy. Physical Review Applied, 2018, 10, .	1.5	85

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37	Integrated silicon qubit platform with single-spin addressability, exchange control and single-shot singlet-triplet readout. Nature Communications, 2018, 9, 4370.	5.8	66
38	Spin and orbital structure of the first six holes in a silicon metal-oxide-semiconductor quantum dot. Nature Communications, 2018, 9, 3255.	5.8	42
39	Logical Qubit in a Linear Array of Semiconductor Quantum Dots. Physical Review X, 2018, 8, .	2.8	39
40	Impact of valley phase and splitting on readout of silicon spin qubits. Physical Review B, 2018, 97, .	1.1	14
41	Gigahertz Single-Electron Pumping Mediated by Parasitic States. Nano Letters, 2018, 18, 4141-4147.	4.5	11
42	Interface-induced spin-orbit interaction in silicon quantum dots and prospects for scalability. Physical Review B, 2018, 97, .	1.1	42
43	Interfacing spin qubits in quantum dots and donorsâ€"hot, dense, and coherent. Npj Quantum Information, 2017, 3, .	2.8	357
44	A single-atom quantum memory in silicon. Quantum Science and Technology, 2017, 2, 015009.	2.6	30
45	Electrically driven spin qubit based on valley mixing. Physical Review B, 2017, 95, .	1.1	34
46	Silicon CMOS architecture for a spin-based quantum computer. Nature Communications, 2017, 8, 1766.	5.8	265
47	Thermal-Error Regime in High-Accuracy Gigahertz Single-Electron Pumping. Physical Review Applied, 2017, 8, .	1.5	37
48	Impact of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>g</mml:mi></mml:math> -factors and valleys on spin qubits in a silicon double quantum dot. Physical Review B, 2017, 96, .	1.1	21
49	Dispersive readout of a silicon quantum dot with an accumulation-mode gate sensor. Applied Physics Letters, 2017, 110, .	1.5	17
50	A dressed spin qubit in silicon. Nature Nanotechnology, 2017, 12, 61-66.	15.6	62
51	Deterministic Atom Placement by Ion Implantation: Few and Single Atom Devices for Quantum Computer Technology. , 2016, , .		4
52	Spin-based quantum computing in silicon CMOS-compatible platforms. , 2016, , .		2
53	Breaking the rotating wave approximation for a strongly driven dressed single-electron spin. Physical Review B, 2016, 94, .	1.1	31
54	Three-waveform bidirectional pumping of single electrons with a silicon quantum dot. Scientific Reports, 2016, 6, 36381.	1.6	7

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55	Valley splitting of single-electron Si MOS quantum dots. Applied Physics Letters, 2016, 109, .	1.5	47
56	Optimization of a solid-state electron spin qubit using gate set tomography. New Journal of Physics, 2016, 18, 103018.	1.2	54
57	Bell's inequality violation with spins in silicon. Nature Nanotechnology, 2016, 11, 242-246.	15.6	56
58	Nonexponential fidelity decay in randomized benchmarking with low-frequency noise. Physical Review A, 2015, 92, .	1.0	46
59	Spin-orbit coupling and operation of multivalley spin qubits. Physical Review B, 2015, 92, .	1.1	69
60	Silicon Metal-oxide-semiconductor Quantum Dots for Single-electron Pumping. Journal of Visualized Experiments, 2015, , e52852.	0.2	10
61	Electron counting in a silicon single-electron pump. New Journal of Physics, 2015, 17, 103030.	1.2	13
62	Single atom devices by ion implantation. Journal of Physics Condensed Matter, 2015, 27, 154204.	0.7	61
63	Electrically controlling single-spin qubits in a continuous microwave field. Science Advances, 2015, 1, e1500022.	4.7	125
64	A two-qubit logic gate in silicon. Nature, 2015, 526, 410-414.	13.7	700
65	Pauli Spin Blockade of Heavy Holes in a Silicon Double Quantum Dot. Nano Letters, 2015, 15, 7314-7318.	4.5	68
66	Quantifying the quantum gate fidelity of single-atom spin qubits in silicon by randomized benchmarking. Journal of Physics Condensed Matter, 2015, 27, 154205.	0.7	107
67	A planar Al-Si Schottky barrier metalâ€“oxideâ€“semiconductor field effect transistor operated at cryogenic temperatures. Applied Physics Letters, 2015, 107, .	1.5	6
68	Single-atom spin qubits in silicon. , 2014, , .		0
69	Observation of single hole transport in a highly tunable silicon quantum dot. , 2014, , .		0
70	Effects of electrostatic confinement in a silicon single-electron pump. , 2014, , .		0
71	High-fidelity adiabatic inversion of a ³¹P electron spin qubit in natural silicon. Applied Physics Letters, 2014, 104, 092115.	1.5	24
72	An addressable quantum dot qubit with fault-tolerant control-fidelity. Nature Nanotechnology, 2014, 9, 981-985.	15.6	703

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73	Coherent Control of a Single<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mmultiscripts><mml:mrow><mml:mi>Si</mml:mi></mml:mrow><mml:mprescripts /><mml:none /><mml:mrow><mml:mn>29</mml:mn></mml:mrow></mml:mmultiscripts></mml:mrow></mml:math>Nuclear Spin Qubit. Physical Review Letters, 2014, 113, 246801.	2.9	47
74	Charge offset stability in Si single electron devices with Al gates. Nanotechnology, 2014, 25, 405201.	1.3	23
75	Charge state hysteresis in semiconductor quantum dots. Applied Physics Letters, 2014, 105, .	1.5	27
76	Storing quantum information for 30 seconds in a nanoelectronic device. Nature Nanotechnology, 2014, 9, 986-991.	15.6	513
77	Sub-Nanoampere One-Shot Single Electron Transistor Readout Electrometry Below 10 Kelvin. IEEE Transactions on Circuits and Systems I: Regular Papers, 2014, 61, 2816-2824.	3.5	11
78	An Accurate Single-Electron Pump Based on a Highly Tunable Silicon Quantum Dot. Nano Letters, 2014, 14, 3405-3411.	4.5	69
79	Single-Shot Readout and Relaxation of Singlet and Triplet States in Exchange-Coupled<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mmultiscripts><mml:mrow><mml:mi mathvariant="normal">P</mml:mi></mml:mrow><mml:mprescripts /><mml:none /><mml:mrow><mml:mn>31</mml:mn></mml:mrow></mml:mmultiscripts></mml:mrow></mml:math>Electron Spins in Silicon. Physical Review Letters, 2014, 112, 236801.	2.9	59
80	A silicon single-electron pump with tunable electrostatic confinement. , 2014, , .		0
81	Designing a large scale quantum computer with atomistic simulations. , 2014, , .		2
82	Silicon quantum electronics. Reviews of Modern Physics, 2013, 85, 961-1019.	16.4	892
83	Single hole transport in a silicon metal-oxide-semiconductor quantum dot. Applied Physics Letters, 2013, 103, .	1.5	23
84	Nanoscale broadband transmission lines for spin qubit control. Nanotechnology, 2013, 24, 015202.	1.3	55
85	Quantum Spintronics: Engineering and Manipulating Atom-Like Spins in Semiconductors. Science, 2013, 339, 1174-1179.	6.0	579
86	High-fidelity readout and control of a nuclear spin qubit in silicon. Nature, 2013, 496, 334-338.	13.7	431
87	Noninvasive Spatial Metrology of Single-Atom Devices. Nano Letters, 2013, 13, 1903-1909.	4.5	29
88	Printed circuit board metal powder filters for low electron temperatures. Review of Scientific Instruments, 2013, 84, 044706.	0.6	28
89	Spin-valley lifetimes in a silicon quantum dot with tunable valley splitting. Nature Communications, 2013, 4, 2069.	5.8	231
90	Coulomb interaction and valley-orbit coupling in Si quantum dots. Physical Review B, 2013, 88, .	1.1	13

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91	Laser-induced short-range disorder in aluminum revealed by ultrafast electron diffuse scattering. Applied Physics Letters, 2013, 103, .	1.5	11
92	A single-atom electron spin qubit in silicon. Nature, 2012, 489, 541-545.	13.7	666
93	Orbital and valley state spectra of a few-electron silicon quantum dot. Physical Review B, 2012, 86, .	1.1	40
94	Design of a RF NEMS switch matrix. , 2011, , .		1
95	Diamond and silicon converge. Nature, 2011, 479, 47-48.	13.7	50
96	Pauli Spin Blockade in a Highly Tunable Silicon Double Quantum Dot. Scientific Reports, 2011, 1, 110.	1.6	86
97	Independent Control of Dot Occupancy and Reservoir Electron Density in a One-electron Quantum Dot. AIP Conference Proceedings, 2011, , .	0.3	0
98	Dynamically controlled charge sensing of a few-electron silicon quantum dot. AIP Advances, 2011, 1, .	0.6	42
99	Charge sharing in multi-electrode devices for deterministic doping studied by IBIC. Nuclear Instruments & Methods in Physics Research B, 2011, 269, 2336-2339.	0.6	5
100	Spin filling of valleyâ€“orbit states in a silicon quantum dot. Nanotechnology, 2011, 22, 335704.	1.3	49
101	Single-electron shuttle based on a silicon quantum dot. Applied Physics Letters, 2011, 98, 212103.	1.5	37
102	Tailoring spectral position and width of field enhancement by focused ion-beam patterning of plasmonic nanoparticles. Physica Status Solidi - Rapid Research Letters, 2010, 4, 262-264.	1.2	15
103	Characterization of SOS-CMOS FETs at Low Temperatures for the Design of Integrated Circuits for Quantum Bit Control and Readout. IEEE Transactions on Electron Devices, 2010, 57, 539-547.	1.6	65
104	Single-shot readout of an electron spin in silicon. Nature, 2010, 467, 687-691.	13.7	623
105	Probe and control of the reservoir density of states in single-electron devices. Physical Review B, 2010, 81, .	1.1	21
106	Electron tunnel rates in a donor-silicon single electron transistor hybrid. Physical Review B, 2010, 81, .	1.1	18
107	Overlapping-gate architecture for silicon Hall bar field-effect transistors in the low electron density regime. Applied Physics Letters, 2010, 97, .	1.5	6
108	Single Ion Implantation into Si-Based Devices. ECS Transactions, 2010, 33, 179-189.	0.3	2

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109	Transport Spectroscopy of Single Phosphorus Donors in a Silicon Nanoscale Transistor. Nano Letters, 2010, 10, 11-15.	4.5	120
110	Electrostatically defined few-electron double quantum dot in silicon. Applied Physics Letters, 2009, 94, .	1.5	54
111	Observation of the single-electron regime in a highly tunable silicon quantum dot. Applied Physics Letters, 2009, 95, .	1.5	77
112	Architecture for high-sensitivity single-shot readout and control of the electron spin of individual donors in silicon. Physical Review B, 2009, 80, .	1.1	80
113	Cylindrical Silicon-on-Insulator Microdosimeter: Design, Fabrication and TCAD Modeling. IEEE Transactions on Nuclear Science, 2009, 56, 424-428.	1.2	13
114	Development and Fabrication of Cylindrical Silicon-on-Insulator Microdosimeter Arrays. IEEE Transactions on Nuclear Science, 2009, 56, 1637-1641.	1.2	10
115	Measuring the Charge and Spin States ofÂElectrons on Individual Dopant Atoms inÂSilicon. Topics in Applied Physics, 2009, , 169-182.	0.4	1
116	Low-Noise Detection System for the Counted Implantation of Single Ions in Silicon. IEEE Transactions on Nuclear Science, 2008, 55, 812-816.	1.2	3
117	Qubit Control-Pulse Generator Circuits for Operation at Cryogenic Temperatures. , 2008, , .		7
118	A silicon radio-frequency single electron transistor at 4.2K. , 2008, , .		1
119	A Cylindrical Silicon-on-Insulator Microdosimeter: Charge Collection Characteristics. IEEE Transactions on Nuclear Science, 2008, 55, 3414-3420.	1.2	25
120	Gate-controlled charge transfer in Si:P double quantum dots. Nanotechnology, 2008, 19, 195402.	1.3	3
121	Bias spectroscopy and simultaneous single-electron transistor charge state detection of Si:P double dots. Nanotechnology, 2008, 19, 265201.	1.3	7
122	Tissue Equivalence Correction in Silicon Microdosimetry for Protons Characteristic of the LEO Space Environment. IEEE Transactions on Nuclear Science, 2008, 55, 3407-3413.	1.2	25
123	A silicon radio-frequency single electron transistor. Applied Physics Letters, 2008, 92, .	1.5	62
124	Quantum bit controller and observer circuits in SOS-CMOS technology for gigahertz low-temperature operation. , 2007, , .		7
125	Scaling of ion implanted Si:P single electron devices. Nanotechnology, 2007, 18, 235401.	1.3	1
126	Single shot charge detection using a radio-frequency quantum point contact. Applied Physics Letters, 2007, 91, .	1.5	67

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127	Gate-Defined Quantum Dots in Intrinsic Silicon. Nano Letters, 2007, 7, 2051-2055.	4.5	205
128	Charge State Control and Relaxation in an Atomically Doped Silicon Device. Nano Letters, 2007, 7, 2000-2003.	4.5	55
129	Integration of Single Ion Implantation Method in Focused Ion Beam System for Nanofabrication. , 2006, , .		1
130	Coulomb blockade in a nanoscale phosphorus-in-silicon island. Microelectronic Engineering, 2006, 83, 1809-1813.	1.1	6
131	Quantum effects in ion implanted devices. Nuclear Instruments & Methods in Physics Research B, 2006, 249, 221-225.	0.6	6
132	Demonstration of a silicon-based quantum cellular automata cell. Applied Physics Letters, 2006, 89, 013503.	1.5	64
133	Ion implanted Si:P double dot with gate tunable interdot coupling. Journal of Applied Physics, 2006, 100, 106104.	1.1	16
134	Controlled single electron transfer between Si:P dots. Applied Physics Letters, 2006, 88, 192101.	1.5	25
135	Nanofabrication of charge-based Si:P quantum computer devices using single-ion implantation. , 2005, , .		1
136	Optimization of single keV ion implantation for the construction of single P-donor devices. , 2005, , .		2
137	Single-electron transistor coupled to a silicon nano-MOSFET. , 2005, , .		1
138	Ion beam induced charge and numerical modeling study of novel detector devices for single ion implantation. Nuclear Instruments & Methods in Physics Research B, 2005, 231, 463-466.	0.6	7
139	Single atom Si nanoelectronics using controlled single-ion implantation. Microelectronic Engineering, 2005, 78-79, 279-286.	1.1	9
140	Modelling single electron transfer in Si:P double quantum dots. Nanotechnology, 2005, 16, 74-81.	1.3	8
141	Single-shot readout with the radio-frequency single-electron transistor in the presence of charge noise. Applied Physics Letters, 2005, 86, 143117.	1.5	32
142	Controlled shallow single-ion implantation in silicon using an active substrate for sub-20â€keV ions. Applied Physics Letters, 2005, 86, 202101.	1.5	180
143	Observing sub-microsecond telegraph noise with the radio frequency single electron transistor. Journal of Applied Physics, 2004, 96, 6827-6830.	1.1	21
144	Development and operation of the twin radio frequency single electron transistor for cross-correlated charge detection. Journal of Applied Physics, 2004, 96, 4508-4513.	1.1	19

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145	Charge-based quantum computing using single donors in semiconductors. Physical Review B, 2004, 69, .	1.1	271
146	TCAD modeling of ion beam induced charge collection in silicon Schottky barrier devices. Nuclear Instruments & Methods in Physics Research B, 2003, 210, 181-185.	0.6	6
147	IBIC characterisation of novel detectors for single atom doping of quantum computer devices. Nuclear Instruments & Methods in Physics Research B, 2003, 210, 186-190.	0.6	5
148	The twin radio frequency single electron transistor for correlated charge detection on microsecond time-scales. Microelectronic Engineering, 2003, 67-68, 775-781.	1.1	7
149	Double-island single-electron transistor for noise-suppressed detection of charge transfer. Microelectronic Engineering, 2003, 67-68, 826-831.	1.1	6
150	Single electron devices for simulating read-out in a solid state quantum computer. Surface Science, 2003, 532-535, 1199-1203.	0.8	1
151	Progress in silicon-based quantum computing. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2003, 361, 1451-1471.	1.6	60
152	Single Phosphorus Ion Implantation into Prefabricated Nanometre Cells of Silicon Devices for Quantum Bit Fabrication. Japanese Journal of Applied Physics, 2003, 42, 4124-4128.	0.8	16
153	Correlated charge detection for readout of a solid-state quantum computer. Applied Physics Letters, 2003, 82, 577-579.	1.5	35
154	Modelling single-electron-transistor-based readout in the Kane solid-state quantum computer. Nanotechnology, 2003, 14, 161-164.	1.3	5
155	Novel Detectors For Single Atom Doping Of Quantum Computer Devices. AIP Conference Proceedings, 2003, , .	0.3	0
156	Technology computer-aided design modelling of single-atom doping for fabrication of buried nanostructures. Nanotechnology, 2003, 14, 157-160.	1.3	13
157	Density-Dependent Spin Polarization in Ultra-Low-Disorder Quantum Wires. Physical Review Letters, 2002, 89, 246801.	2.9	150
158	Single-electron transistor architectures for charge motion detection in solid-state quantum computer devices. Smart Materials and Structures, 2002, 11, 749-755.	1.8	3
159	A self-aligned fabrication process for silicon quantum computer devices. Nanotechnology, 2002, 13, 686-690.	1.3	7
160	Scanning tunnelling microscope fabrication of arrays of phosphorus atom qubits for a silicon quantum computer. Smart Materials and Structures, 2002, 11, 741-748.	1.8	8
161	Nanoscale fabrication using single-ion impacts. Smart Materials and Structures, 2002, 11, 686-690.	1.8	5
162	Nanofabrication processes for single-ion implantation of silicon quantum computer devices. Smart Materials and Structures, 2002, 11, 735-740.	1.8	6

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163	Single ion implantation in the quantum computer construction project. , 2002, , .		0
164	Modelling of electrostatic gate operations in the Kane solid state quantum computer. Microelectronics Journal, 2002, 33, 1053-1058.	1.1	8
165	<title>Nanoscale phosphorous atom arrays created using STM for the fabricaton of a silicon-based quantum computer</title>. , 2001, , .		0
166	Modeling of electrostatic gate operations in the Kane solid state quantum computer. , 2001, , .		0
167	<title>Nanofabrication processes for single-ion implantation of silicon quantum computer devices</title>. , 2001, , .		1
168	<title>Nanoscale fabrication using single-ion impacts</title>. , 2001, 4590, 173.		2
169	Many-body spin-related phenomena in ultra low-disorder quantum wires. Physical Review B, 2001, 63, .	1.1	139
170	Towards the fabrication of phosphorus qubits for a silicon quantum computer. Physical Review B, 2001, 64, .	1.1	174
171	Experimental determination of theBâˆ’Tphase diagram ofYBa2Cu3O7âˆ’Îto 150 T forBâŠ¥c. Physical Review B, 2000, 61, 1584-1587.	1.1	36
172	Single-spin measurement using single-electron transistors to probe two-electron systems. Physical Review B, 2000, 61, 2961-2972.	1.1	103
173	Many-body Spin Interactions in Semiconductor Quantum Wires. Australian Journal of Physics, 2000, 53, 543.	0.6	1
174	Evidence for ballistic electron transport exceeding 160 Î¼m in an undopedGaAs/AlxGa1âˆ’xAsfield-effect transistor. Physical Review B, 1999, 59, 4622-4625.	1.1	14
175	Quantum point contact in a magnetic field: Far-infrared resonant heating observed in photoconductivity. Applied Physics Letters, 1999, 75, 3150-3152.	1.5	5
176	Quantized conductance in quantum wires with gate-controlled width and electron density. Applied Physics Letters, 1998, 72, 3506-3508.	1.5	125
177	Transport measurements of in-plane critical fields inYBa2Cu3O7âˆ’Îto 300 T. Physical Review B, 1998, 57, R14084-R14087.	1.1	24
178	Thermoelectric signature of the excitation spectrum of a quantum dot. Physical Review B, 1997, 55, R10197-R10200.	1.1	97
179	Measurement instrumentation for electrical transport experiments in extreme pulsed magnetic fields generated by flux compression. Review of Scientific Instruments, 1997, 68, 3843-3860.	0.6	17
180	Magnetoresistance and magnetic breakdown in the quasi-two-dimensional conductors(BEDTâˆ’TTF)2MHg(SCN)4[M=K,Rb,Tl]. Physical Review B, 1996, 54, R8289-R8292.	1.1	26

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181	Observation of the effect of electron-electron scattering on the impurity-limited resistivity of a two-dimensional electron gas. Physical Review B, 1995, 51, 13793-13796.	1.1	10
182	Conductance in Quantum Boxes: Interference and Single Electron Effects. NATO ASI Series Series B: Physics, 1995, , 201-216.	0.2	1
183	Observation of Coulomb blockade oscillations in the thermopower of a quantum dot. Solid State Communications, 1993, 87, 1145-1149.	0.9	66
184	Transport by single and few electrons in GaAs mesoscopic structures. Physica A: Statistical Mechanics and Its Applications, 1993, 200, 65-79.	1.2	3
185	Thermopower of a one-dimensional ballistic constriction in the non-linear regime. Journal of Physics Condensed Matter, 1993, 5, 8055-8064.	0.7	22
186	Two-dimensional electron-gas heating and phonon emission by hot ballistic electrons. Physical Review B, 1992, 45, 6309-6312.	1.1	20
187	Overlapping-Gate Architecture for Silicon Hall Bar MOSFET Devices in the Low Electron Density and High Magnetic Field Regime. Materials Science Forum, 0, 700, 93-95.	0.3	0